

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7), V <sub>GS</sub> = -10V	I <sub>D</sub>	-1.5 -1.2	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-6	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P <sub>D</sub>	0.72	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6)	R <sub>θJA</sub>	176	°C/W
Power Dissipation (Note 7)	P <sub>D</sub>	1.17	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 7)	R <sub>θJA</sub>	108	°C/W
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	34	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1.0	μA	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	-1.8	-3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	257 343	350 550	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -0.9A V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -0.8A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.8	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	206	—	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	15	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	11	—	pF	
Gate Resistance	R <sub>g</sub>	—	17	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	2.0	—	nC	V <sub>DS</sub> = -30V, I <sub>D</sub> = -0.9A
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	4.1	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	0.5	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.8	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.6	—	ns	V <sub>DD</sub> = -30V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -1.0A, R <sub>g</sub> = 6Ω
Turn-On Rise Time	t <sub>R</sub>	—	3.8	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	12.3	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	7.3	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	8.2	—	ns	I <sub>S</sub> = -1.0A, di/dt = -100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	2.7	—	nC	I <sub>S</sub> = -1.0A, di/dt = -100A/μs

- Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.  
8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.

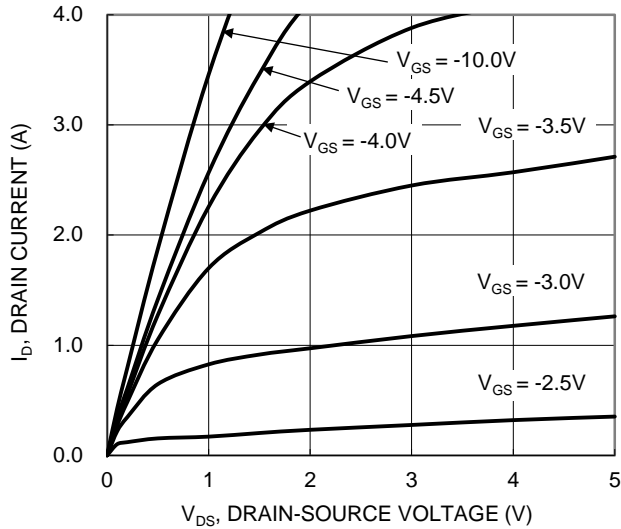


Figure 1. Typical Output Characteristic

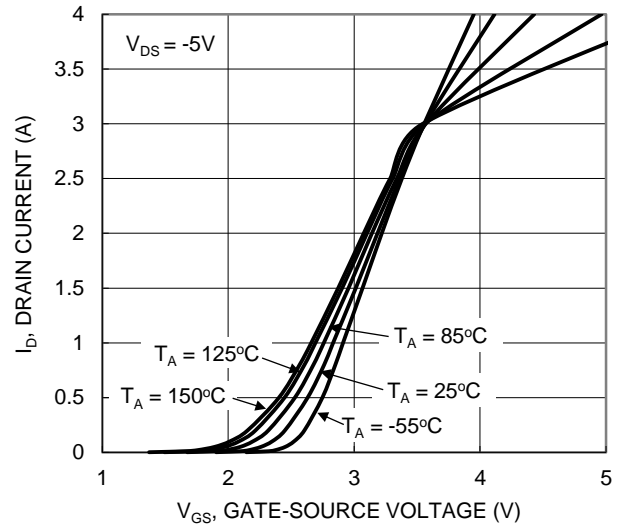


Figure 2. Typical Transfer Characteristic

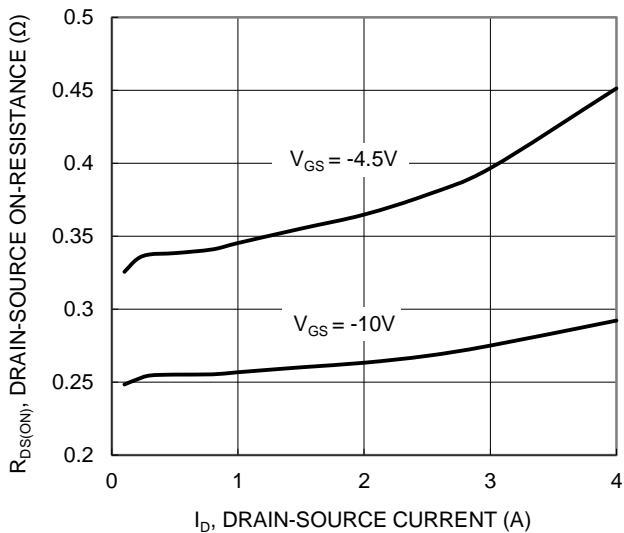


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

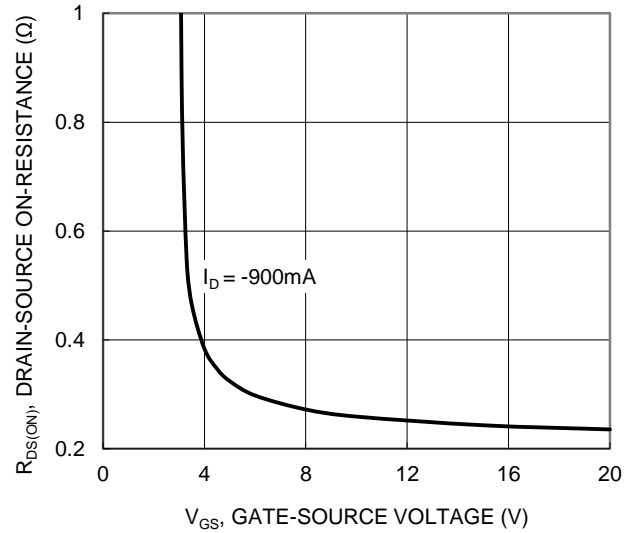


Figure 4. Typical Transfer Characteristic

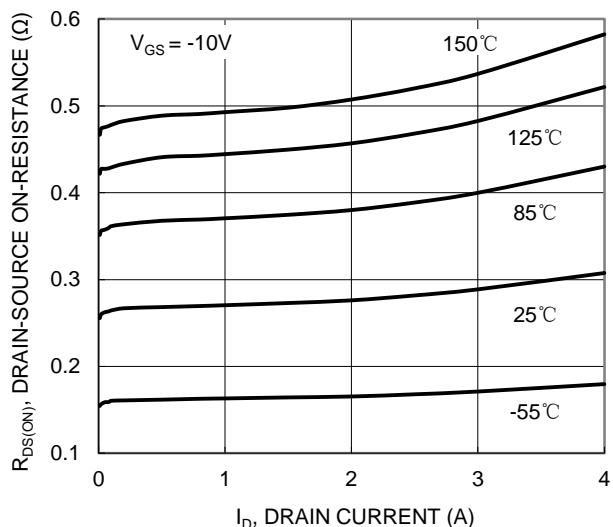


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

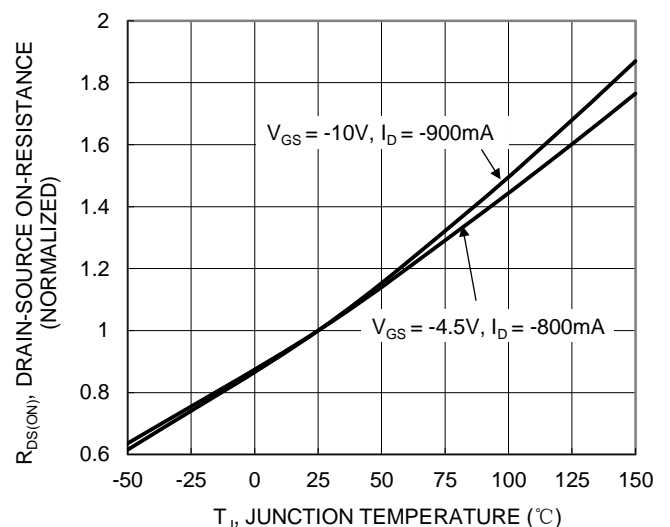


Figure 6. On-Resistance Variation with Junction Temperature

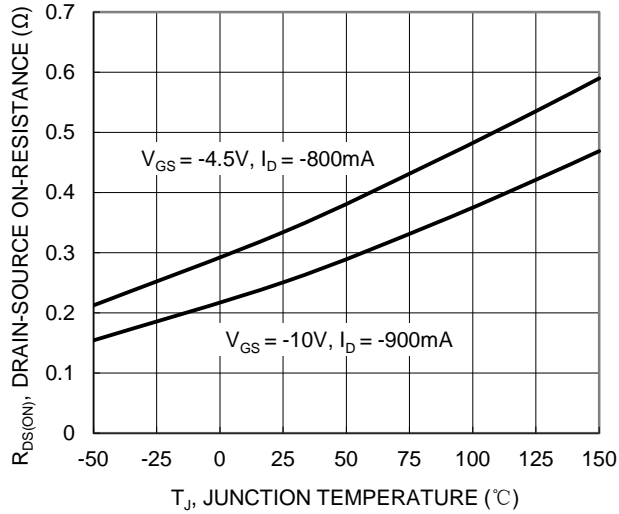


Figure 7. On-Resistance Variation with Junction Temperature

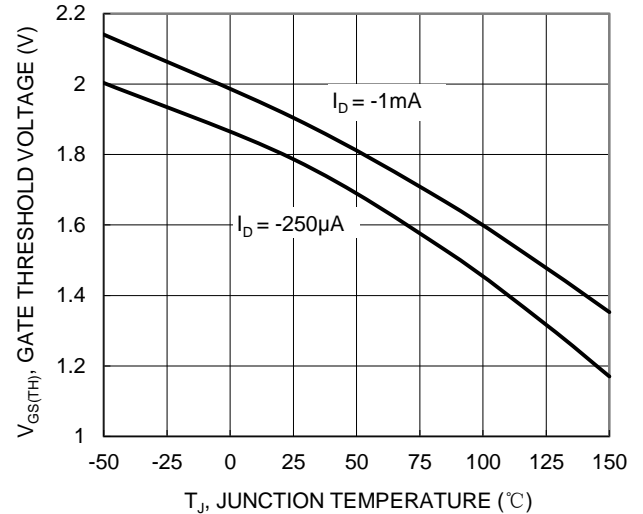


Figure 8. Gate Threshold Variation vs. Junction Temperature

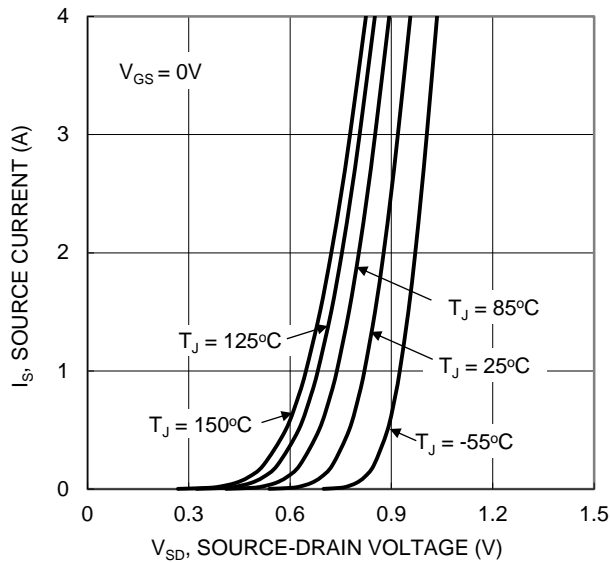


Figure 9. Diode Forward Voltage vs. Current

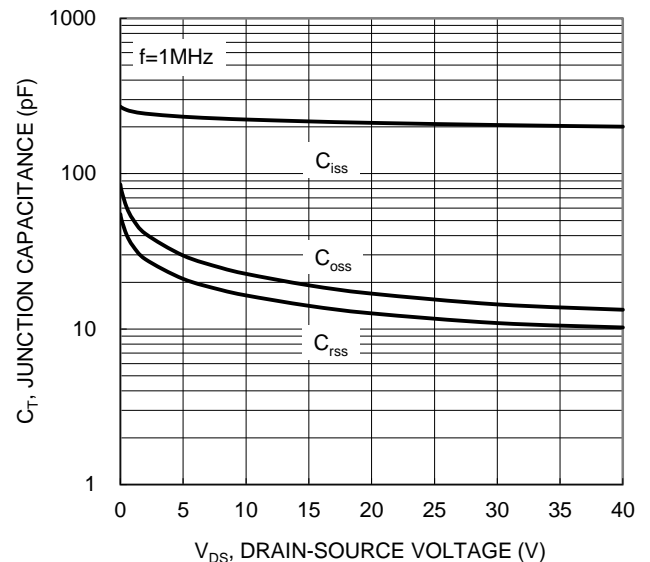


Figure 10. Typical Junction Capacitance

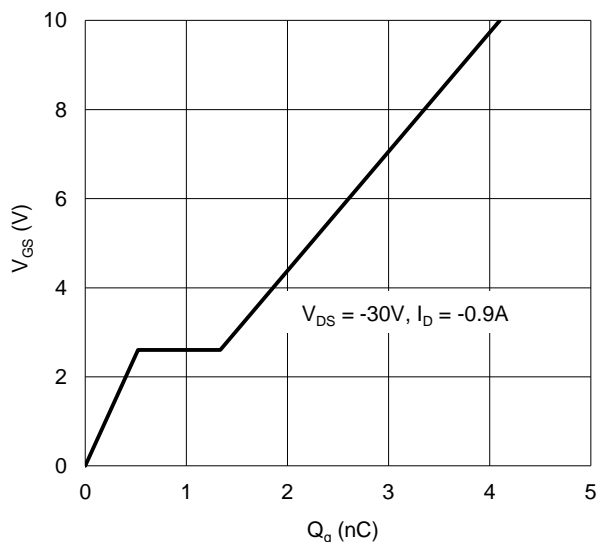


Figure 11. Gate Charge

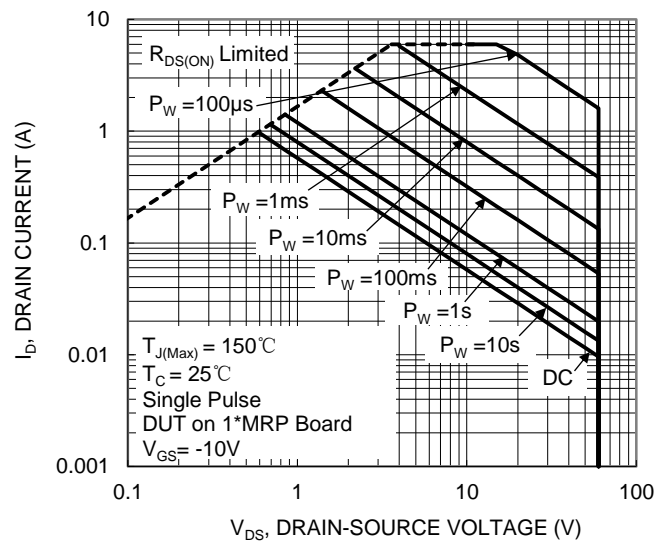


Figure 12. SOA, Safe Operation Area

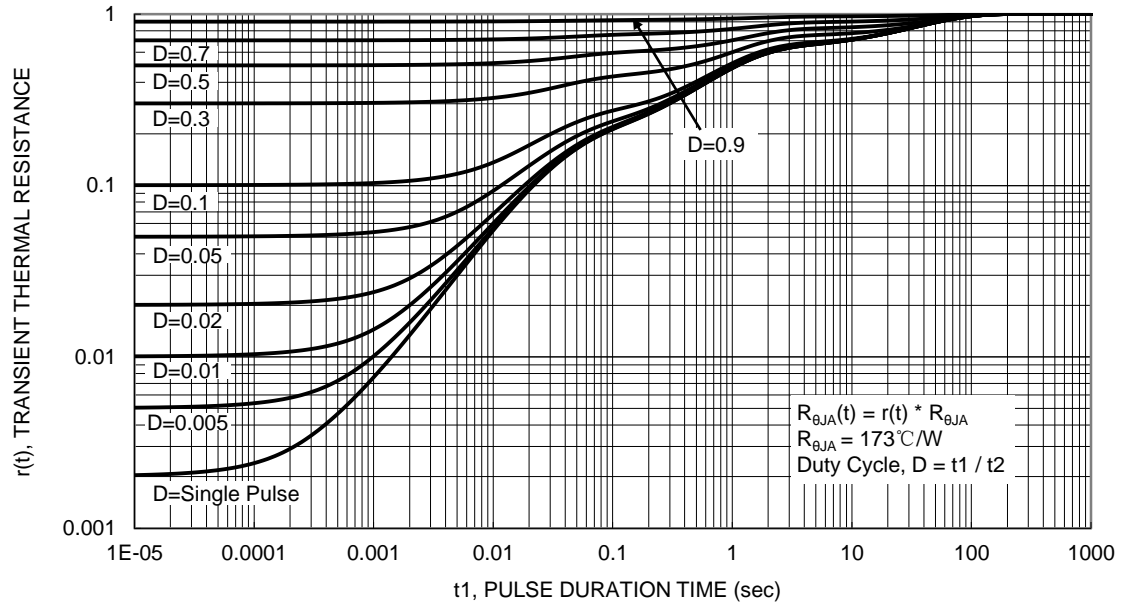
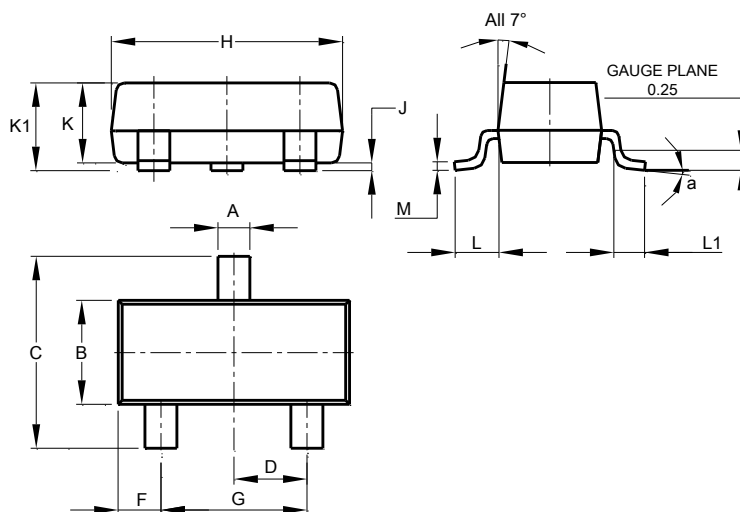


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**

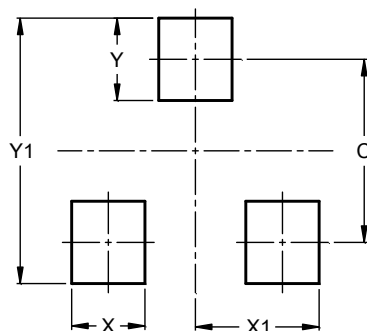


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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